

32. (Three times amended) A polishing pad assembly for polishing a semiconductor wafer, said assembly comprising:

a belt forming a closed loop; and

at least one chemical mechanical planarization polishing pad mounted on the belt,

the chemical mechanical planarization polishing pad adapted to receive a polishing slurry;

wherein said belt is formed of metal.

34. (Three times amended) A polishing pad assembly for polishing a semiconductor wafer, said assembly comprising:

a first roller;

at least one additional roller;

a belt forming a closed loop, which belt is mounted on said first roller and said at least one additional roller;

at least one chemical mechanical planarization polishing pad mounted to said belt,

the chemical mechanical planarization polishing pad adapted to receive a polishing slurry;

and

a drive system coupled to at least said first roller to rotate said first roller and to cause said belt and said chemical mechanical planarization polishing pad to move in a path;

wherein said belt is formed of metal.

36. (Twice amended) A polishing pad assembly for polishing a semiconductor wafer, said assembly comprising:

a belt forming a closed loop; and

at least one chemical mechanical planarization polishing pad mounted on the belt,

having no fixed abrasive layer

the chemical mechanical planarization polishing pad adapted to receive a polishing slurry;

wherein said belt comprises a polyurethane material.

37. (Twice amended) A polishing pad assembly for polishing a semiconductor wafer, said assembly comprising:

a first roller;

at least one additional roller;

a belt forming a closed loop, which belt is mounted on said first roller and said at least one additional roller;

at least one chemical mechanical planarization polishing pad mounted to said belt,

the chemical mechanical planarization polishing pad adapted to receive a polishing slurry;

and

a drive system coupled to at least said first roller to rotate said first roller and to cause said belt and said chemical mechanical planarization polishing pad to move in a path;

wherein said belt comprises a polyurethane material.

38. (Twice amended) A polishing pad assembly for polishing a semiconductor wafer, said assembly comprising:

a belt forming a closed loop; and

at least one chemical mechanical planarization polishing pad mounted on the belt,
the chemical mechanical planarization polishing pad adapted to receive a polishing
slurry;

wherein said belt comprises a high-strength polymer.

40. (Twice amended) A polishing pad assembly for polishing a semiconductor wafer, said assembly comprising:

a first roller;

at least one additional roller;

a belt forming a closed loop, which belt is mounted on said first roller and said at least one additional roller;

at least one chemical mechanical planarization polishing pad mounted to said belt,
the chemical mechanical planarization polishing pad adapted to receive a polishing
slurry;

and

a drive system coupled to at least said first roller to rotate said first roller and to cause said belt and said chemical mechanical planarization polishing pad to move in a path;

wherein said belt comprises a high-strength material.